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(Use several sheets if necessary)ATTY DOCKET NO.
35.C10530C/D2APPLICATION NO.
Div. of 08/863,717APPLICANT
KIYOFUMI SAKAGUCHI, ET AL.FILING DATE
September 29, 1998GROUP
NYA

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	5466631	11/95	Ichikawa, et al.	—	—	
G	5453394	9/95	Yonehara, et al.	—	—	
G	5277748	1/94	Sakaguchi, et al.	—	—	
G	4727047	2/23/88	Bozler, et al.	437	89	
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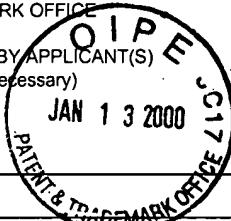
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APPLICANT...KIYOFUMI SAKAGUCHI ET AL.

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